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# **Power Booster Amplifier**



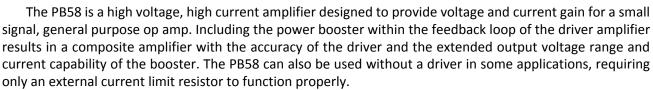
### **FEATURES**

- Wide Supply Range ±15V to ±150V
- High Output Current —
   1.5A Continuous (PB58)
   2.0A Continuous (PB58A)
- Voltage and Current Gain
- High Slew Rate 50V/μs typical (PB58)
   75V/μs minimum (PB58A)
- Programmable Output Current Limit
- High Power Bandwidth 320 kHz typical
- Low Quiescent Current 12mA typical
- Evaluation Kit See EK50



- High Voltage Instrumentation
- Electrostatic Transducers & Deflection
- Programmable Power Supplies up to 280V p-p





The output stage utilizes complementary MOSFETs, providing symmetrical output impedance and eliminating second breakdown limitations imposed by Bipolar Transistors. Internal feedback and gainset resistors are provided for a pin-strapable gain of 3. Additional gain can be achieved with a single external resistor. Compensation is not required for most driver/gain configurations, but can be accomplished with a single external capacitor. Enormous flexibility is provided through the choice of driver amplifier, current limit, supply voltage, voltage gain, and compensation.

This hybrid circuit utilizes a beryllia (BeO) substrate, thick film resistors, ceramic capacitors and semiconductor chips to maximize reliability, minimize size and give top performance.

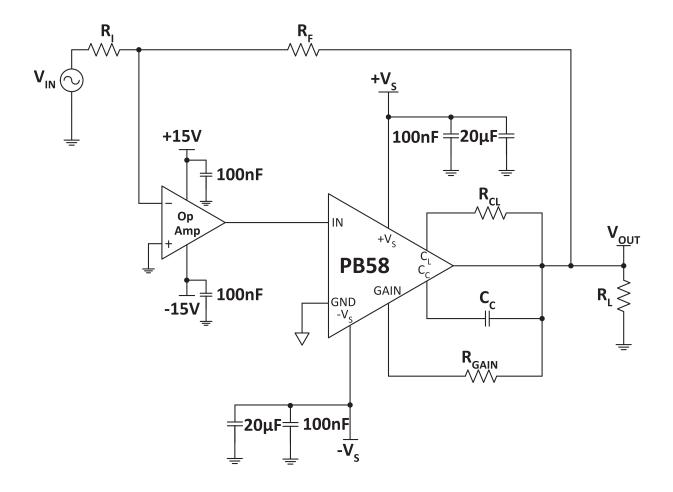
Ultrasonically bonded aluminum wires provide reliable interconnections at all operating temperatures. The 8-pin TO-3 package is electrically isolated and hermetically sealed using one-shot resistance welding. The use of compressible isolation washers voids the warranty.





# **TYPICAL CONNECTION**

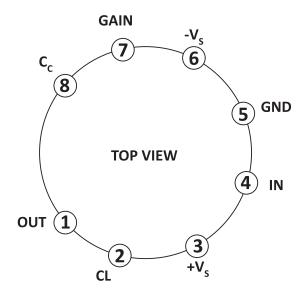
Figure 1: Typical Connection





# PINOUT AND DESCRIPTION TABLE

**Figure 2: External Connections** 



Pin Number	Name	Description
1	OUT	The output. Connect this pin to load and to the feedback resistors.
2	CL	Connect to the current limit resistor. Output current flows into/out of these pins through $R_{\text{CL}}$ . The output pin and the load are connected to the other side of $R_{\text{CL}}$ .
3	+Vs	The positive supply rail.
4	IN	The input.
5	GND	Ground. Connect to same ground as referenced by input amplifier.
6	-Vs	The negative supply rail.
7	GAIN	Gain resistor pin. Connect R <sub>GAIN</sub> between GAIN and OUT. This will specify the gain for the power booster itself, not the composite amplifier. See applicable section.
8	СС	Compensation capacitor connection. Select value based on Phase Compensation.  See applicable section.

# PB58 • PB58A



### **SPECIFICATIONS**

The power supply voltage specified under typical (TYP) applies,  $T_C = 25$ °C unless otherwise noted.

### ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Min	Max	Units
Supply Voltage, total	+V <sub>s</sub> to -V <sub>s</sub>		300	V
Output Current, within SOA	I <sub>O</sub>		2	А
Power Dissipation, continuous @ $T_c = 25^{\circ}C^{1}$	P <sub>D</sub>		83	W
Input Voltage, referred to COM	V <sub>IN</sub>		±15	V
Temperature, pin solder, 10s max.			350	°C
Temperature, junction <sup>1</sup>	T <sub>J</sub>		175	°C
Temperature Range, storage		-65	+150	°C
Operating Temperature Range, case	T <sub>C</sub>	-55	+125	°C

<sup>1.</sup> Long term operation at the maximum junction temperature will result in reduced product life. Derate internal power dissipation to achieve high MTTF (Mean Time to Failure).



The PB58 is constructed from MOSFET transistors. ESD handling procedures must be observed. The internal substrate contains beryllia (BeO). Do not break the seal. If accidentally broken, do not crush, machine, or subject to temperatures in excess of 850°C to avoid generating toxic fumes.

### **INPUT**

Parameter	Test	PB58		PB58A			Units	
raidilietei	Conditions	Min	Тур	Max	Min	Тур	Max	Offics
Offset Voltage, initial			±0.75	±1.75		*	±1.0	V
Offset Voltage vs. Temperature	Full temp range <sup>1</sup>		-4.5	-7		*	*	mV/°C
Input Impedance, DC		25	50		*	*		kΩ
Input Capacitance			3			*		pF
Closed Loop Gain Range		3	10	25	*	*	*	V/V
Gain Accuracy, internal Rg, Rf	A <sub>V</sub> = 3		±10	±15		*	*	%
Gain Accuracy, external Rf	A <sub>V</sub> = 10		±15	±25		*	*	%
Phase Shift	f = 10 kHz, AV <sub>CL</sub> = 10, C <sub>C</sub> = 22pF		10			*		o
riidse siiiit	f = 200 kHz, AV <sub>CL</sub> = 10, C <sub>C</sub> = 22pF		60			*		o

<sup>1.</sup> Guaranteed by design but not tested.



## **OUTPUT**

Parameter	Test	PB58			PB58A			Units
raiailletei	Conditions	Min	Тур	Max	Min	Тур	Max	Ollits
Voltage Swing	Io = 1.5A (PB58), 2A (PB58A)	V <sub>S</sub> -11	V <sub>S</sub> -8		V <sub>S</sub> -15	V <sub>S</sub> -11		V
Voltage Swing	Io = 1A	V <sub>S</sub> -10	V <sub>S</sub> –7		*	*		V
Voltage Swing	Io = 0.1A	V <sub>S</sub> -8	V <sub>S</sub> –5		*	*		V
Current, continuous		1.5			2			Α
Slew Rate	Full temp range	50	100		75	*		V/µs
Capacitive Load	Full temp range		2200			*		pF
Settling Time to 0.1%	$R_L$ = 100 Ω, 2V step		2			*		μs
Power Bandwidth	V <sub>C</sub> = 100 Vpp	160	320		240	*		kHz
Small Signal Bandwidth	$C_C = 22pF, A_V = 25,$ Vcc = ±100		100			*		kHz
Small Signal Bandwidth	$C_C = 22pF, A_V = 3,$ Vcc = ±30		1			*		MHz

### **POWER SUPPLY**

Parameter	Test	PB58			PB58A			Units
raiailletei	Conditions	Min	Тур	Max	Min	Тур	Max	Offics
Voltage, ±V <sub>S</sub> <sup>1</sup>	Full temp range	±15 <sup>2</sup>	±60	±150	*	*	*	V
	V <sub>S</sub> = ±15		11			*		mA
Current, quiescent	V <sub>S</sub> = ±60		12			*		mA
	V <sub>S</sub> = ±150		14	18		*	*	mA

- 1.  $+V_S$  and  $-V_S$  denote the positive and negative supply rail respectively.
- 2. +V<sub>S</sub>/-V<sub>S</sub> must be at least 15V above/below COM.

# PB58 • PB58A



## **THERMAL**

Parameter	Test	PB58			PB58A			Units
raiametei	Conditions	Min	Тур	Max	Min	Тур	Max	Offics
Resistance, AC, junction to case <sup>1</sup>	Full temp range, f > 60 Hz		1.2	1.3		*	*	°C/W
Resistance, DC, junction to case	Full temp range, f < 60 Hz		1.6	1.8		*	*	°C/W
Resistance, junction to air	Full temp range		30			*		°C/W
Temperature Range, case	Meets full range specs	-25	25	85	*	*	*	°C

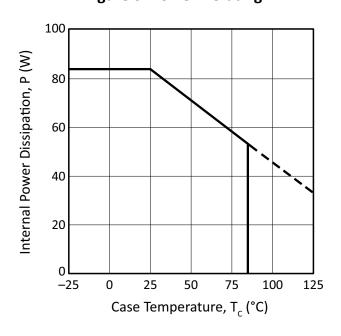
<sup>1.</sup> Rating applies if the output current alternates between both output transistors at a rate faster than 60 Hz.

**Note:** \* The specification of PB58A is identical to the specification for PB58 in applicable column to the left.

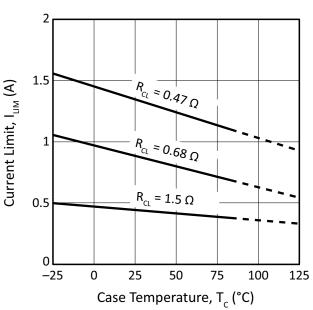


## **TYPICAL PERFORMANCE GRAPHS**

Figure 3: Power Derating



**Figure 4: Current Limit** 



**Figure 5: Output Voltage Swing** 

Noltage Drop From Supply, V. - N. 15 1 1.5 2
Output Current, Io (A)

Figure 6: Small Signal Response

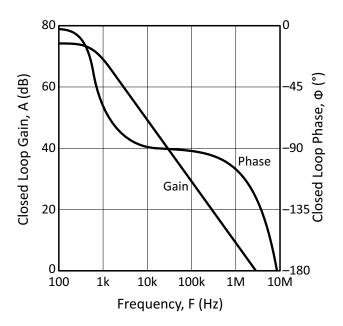




Figure 7: Small Signal Response

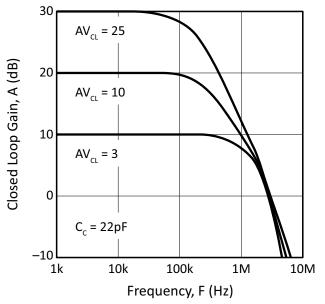
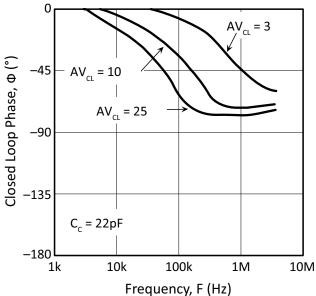


Figure 8: Small Signal Response



**Figure 9: Quiescent Current** 

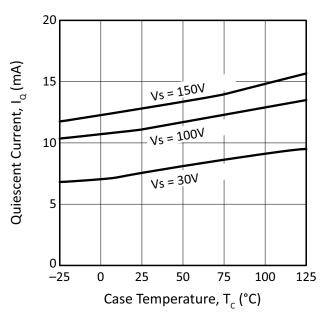


Figure 10: Input Offset Voltage

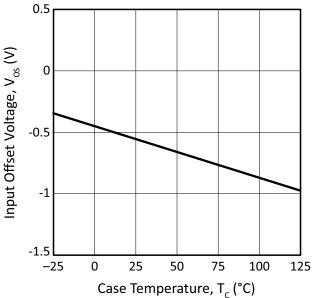




Figure 11: Slew Rate vs. Temperature

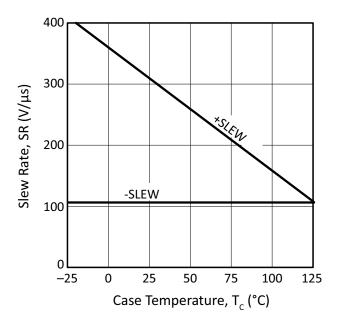


Figure 13: Pulse Response

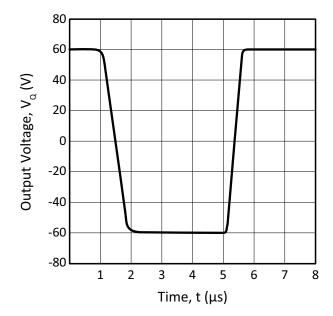


Figure 12: Power Response

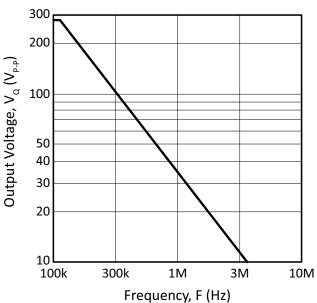
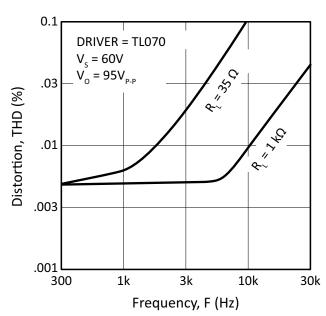


Figure 14: Harmonic Distortion

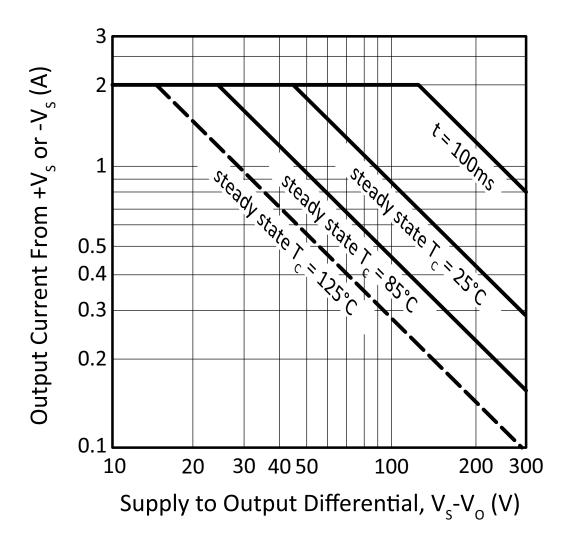




# **SAFE OPERATING AREA (SOA)**

**Note:** The output stage is protected against transient flyback. However, for protection against sustained, high energy flyback, external fast-recovery diodes should be used.

Figure 15: SOA



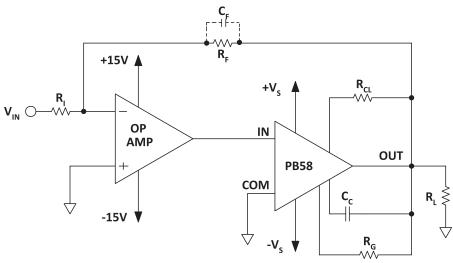


### **GENERAL**

Please read Application Note 1 "General Operating Considerations" which covers stability, supplies, heat sinking, mounting, current limit, SOA interpretation, and specification interpretation. Visit www.apexanalog.com for Apex Microtechnology's complete Application Notes library, Technical Seminar Workbook, and Evaluation Kits.

### TYPICAL APPLICATION

Figure 16: Typical Application



### **CURRENT LIMIT**

For proper operation, the current limit resistor ( $R_{CL}$ ) must be connected as shown in the external connection diagram. The minimum value is  $0.33\Omega$  with a maximum practical value of  $47\Omega$ . For optimum reliability the resistor value should be set as high as possible. The value is calculated as follows:

$$I_{CL} = \frac{0.65 V}{R_{CL}} + 0.01 A$$
  $-I_{CL} = \frac{0.65 V}{R_{CL}}$ 

### **COMPOSITE AMPLIFIER CONSIDERATIONS**

Cascading two amplifiers within a feedback loop has many advantages, but also requires careful consideration of several amplifier and system parameters. The most important of these are gain, stability, slew rate, and output swing of the driver. Operating the booster amplifier in higher gains results in a higher slew rate and lower output swing requirement for the driver, but makes stability more difficult to achieve.



### **GAIN SET**

$$R_G = [(Av - 1) \cdot 3.1k] - 6.2k[\Omega]$$

$$Av = \frac{R_G + 6.2k}{3.1k} + 1$$

The booster's closed-loop gain is given by the equation above. The composite amplifier's closed loop gain is determined by the feedback network, that is: –Rf/Ri (inverting) or 1+Rf/Ri (non-inverting). The driver amplifier's "effective gain" is equal to the composite gain divided by the booster gain.

Example: Inverting configuration (figure 1) with

R i = 2 k, R f = 60 k, R g = 0:

Av (booster) = (6.2 k/ 3.1 k) + 1 = 3

Av (composite) = 60 k/2 k = -30

Av (driver) = -30/3 = -10

### **STABILITY**

Stability can be maximized by observing the following guidelines:

- 1. Operate the booster in the lowest practical gain.
- 2. Operate the driver amplifier in the highest practical effective gain.
- 3. Keep gain-bandwidth product of the driver lower than the closed loop bandwidth of the booster.
- 4. Minimize phase shift within the loop.

A good compromise for (1) and (2) is to set booster gain from 3 to 10 with total (composite) gain at least a factor of 3 times booster gain. Guideline (3) implies compensating the driver as required in low composite gain configurations. Phase shift within the loop (4) is minimized through use of booster and loop compensation capacitors Cc and Cf when required. Typical values are 5pF to 33pF.

Stability is the most difficult to achieve in a configuration where driver effective gain is unity (ie; total gain = booster gain). For this situation, The table below gives compensation values for optimum square wave response with the op amp drivers listed.

Driver	C <sub>CH</sub>	C <sub>F</sub>	c <sub>c</sub>	FPBW	SR	
0P07	-	22p	22p	4 kHz	1.5	
741	-	18p	10p	20 kHz	7	
LF155	-	4.7p	10p	60 kHz	>60	
LF156	-	4.7p	10p	80 kHz	>60	
TL070	22p	15p	10p	80 kHz	>60	
_	For: R <sub>r</sub> = 33 k, R <sub>s</sub> = 3.3 k, R <sub>o</sub> = 22 k					



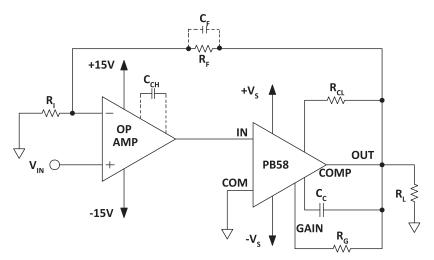


Figure 17: Non-Inverting Composite Amplifier

### **SLEW RATE**

The slew rate of the composite amplifier is equal to the slew rate of the driver times the booster gain, with a maximum value equal to the booster slew rate.

### **OUTPUT SWING**

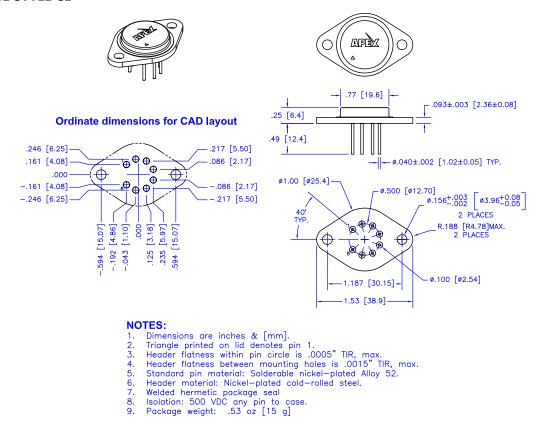
The maximum output voltage swing required from the driver op amp is equal to the maximum output swing from the booster divided by the booster gain. The Vos of the booster must also be supplied by the driver, and should be subtracted from the available swing range of the driver. Note also that effects of Vos drift and booster gain accuracy should be considered when calculating maximum available driver swing.



#### PACKAGE OPTIONS

Part Number	Apex Package Style	Description
PB58	CE	8-pin TO-3
PB58A	CE	8-pin TO-3

#### PACKAGE STYLE CE



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